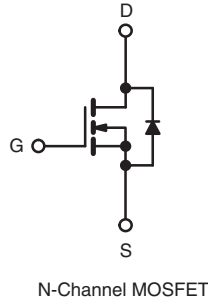
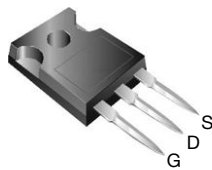


## E Series Power MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V) at $T_J$ max.	650
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10\text{ V}$   0.064
$Q_g$ max. (nC)	220
$Q_{gs}$ (nC)	36
$Q_{gd}$ (nC)	60
Configuration	Single

**TO-247AC**


### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low Figure-of-Merit (FOM)  $R_{on} \times Q_g$
- Low Input Capacitance ( $C_{iss}$ )
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge ( $Q_g$ )
- Avalanche Energy Rated (UIS)
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
  - High-Intensity Discharge (HID)
  - Fluorescent Ballast Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
  - Renewable Energy
  - Solar (PV Inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and Halogen-free	SiHG47N60E-GE3


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	600	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Gate-Source Voltage AC ( $f > 1\text{ Hz}$ )		30		
Continuous Drain Current ( $T_J = 150\text{ }^\circ\text{C}$ )	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	47	A
		$T_C = 100\text{ }^\circ\text{C}$	30	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	145		
Linear Derating Factor		3	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	1500	mJ	
Maximum Power Dissipation	$P_D$	357	W	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Drain-Source Voltage Slope	$dV/dt$	$T_J = 125\text{ }^\circ\text{C}$	37	V/ns
Reverse Diode $dV/dt^d$		11		
Soldering Recommendations (Peak Temperature)	for 10 s	300 $^\circ$	$^\circ\text{C}$	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 73.5\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 6.4\text{ A}$ .
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100\text{ A}/\mu\text{s}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ .



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.33	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		600	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 250\text{ }\mu\text{A}$		-	0.66	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 24\text{ A}$	-	0.053	0.064	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 8\text{ V}, I_D = 3\text{ A}$		-	6.8	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	4810	-	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	230	-	
Reverse Transfer Capacitance	$C_{rss}$			-	5	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 47\text{ A}, V_{DS} = 480\text{ V}$	-	147	220	nC
Gate-Source Charge	$Q_{gs}$			-	36	-	
Gate-Drain Charge	$Q_{gd}$			-	60	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 480\text{ V}, I_D = 47\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.4\text{ }\Omega$		-	24	50	ns
Rise Time	$t_r$			-	11	25	
Turn-Off Delay Time	$t_{d(off)}$			-	94	140	
Fall Time	$t_f$			-	13	26	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$		-	0.65	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	47	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	140	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 47\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 47\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	696	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	16	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	39	-	A

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

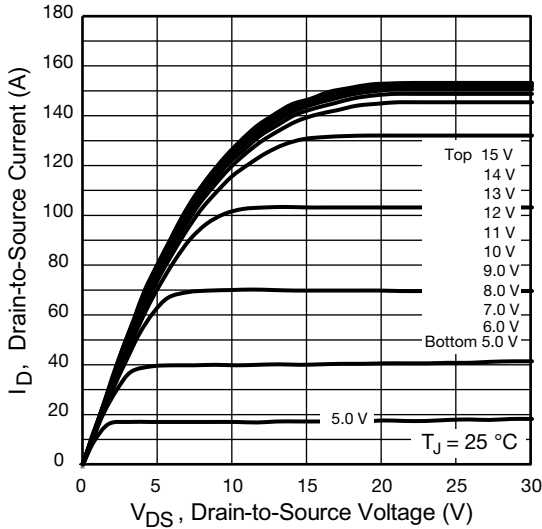


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

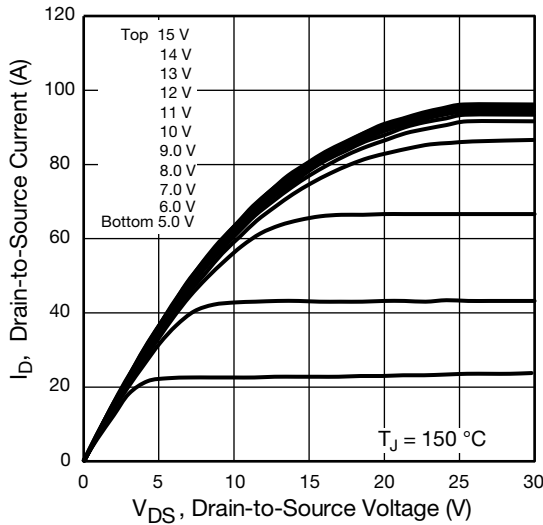


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

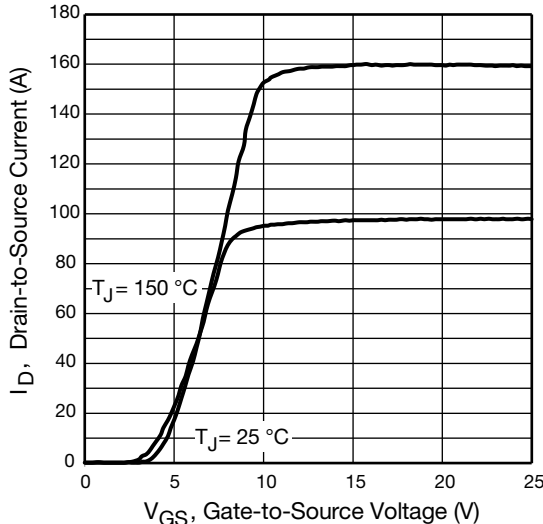


Fig. 3 - Typical Transfer Characteristics

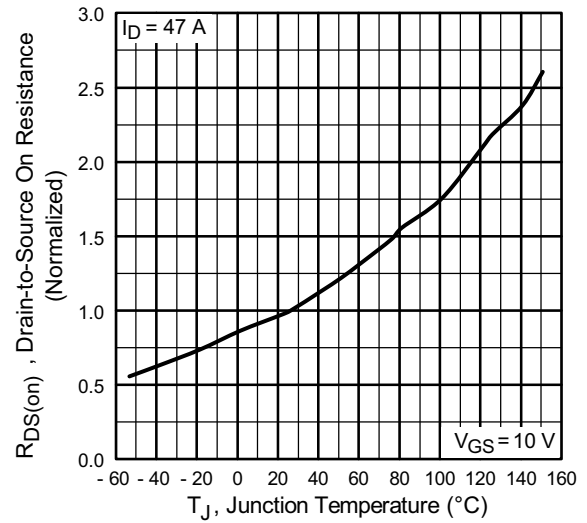


Fig. 4 - Normalized On-Resistance vs. Temperature

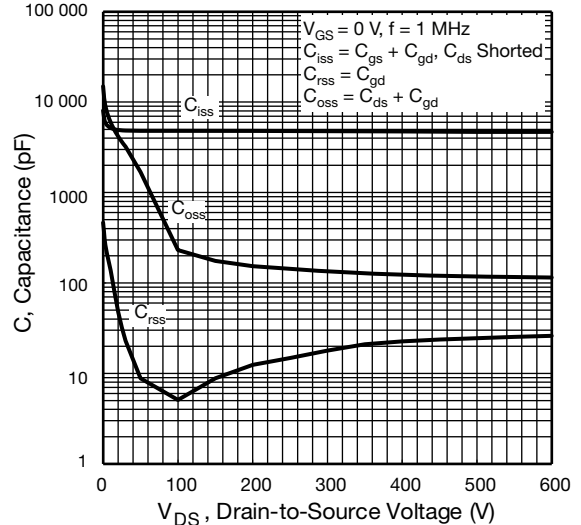


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

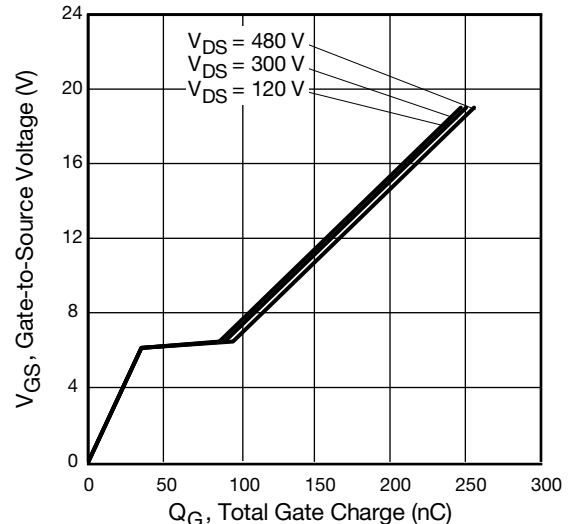


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

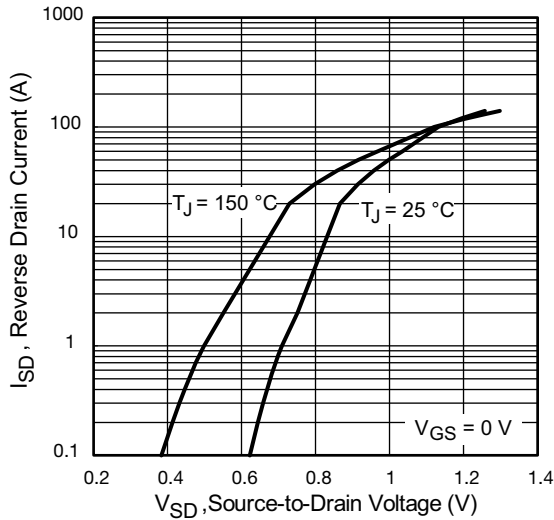


Fig. 7 - Typical Source-Drain Diode Forward Voltage

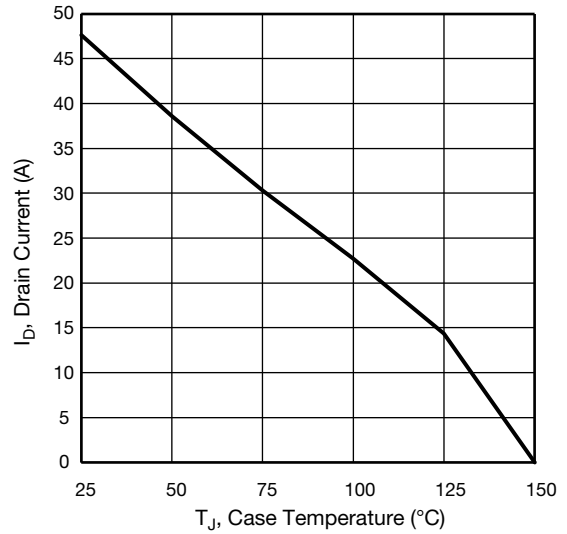


Fig. 9 - Maximum Drain Current vs. Case Temperature

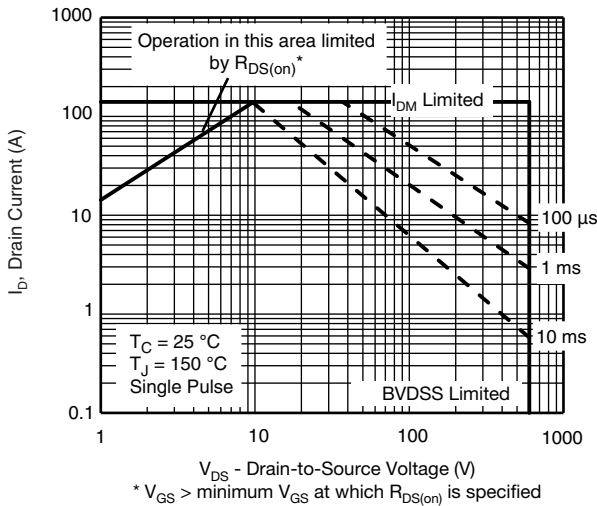


Fig. 8 - Maximum Safe Operating Area

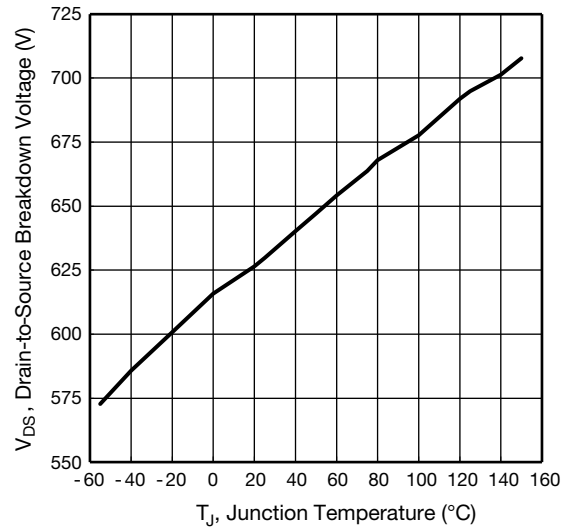


Fig. 10 - Temperature vs. Drain-to-Source Voltage

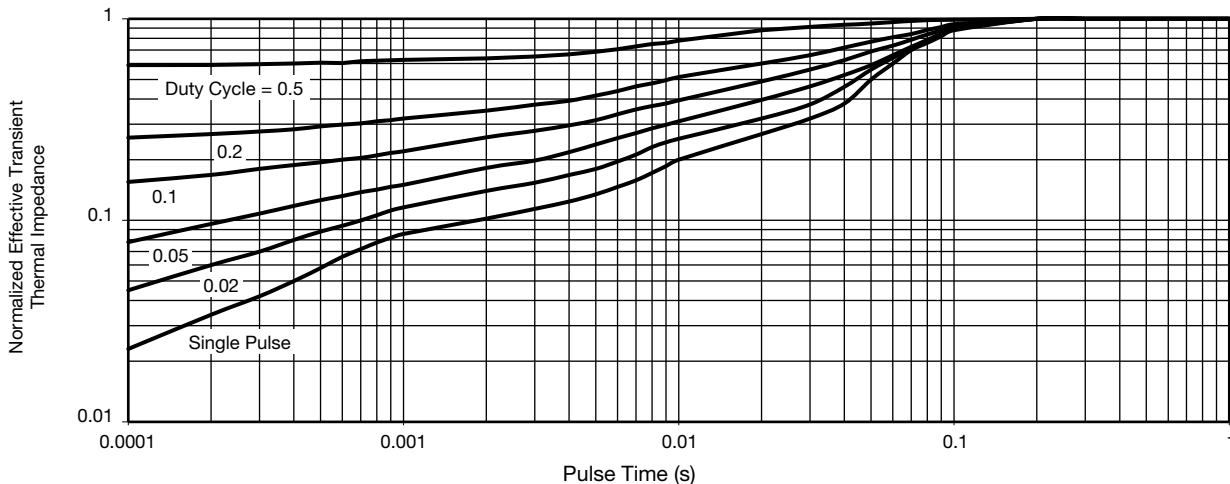


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

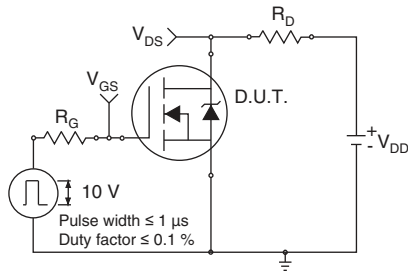


Fig. 12 - Switching Time Test Circuit

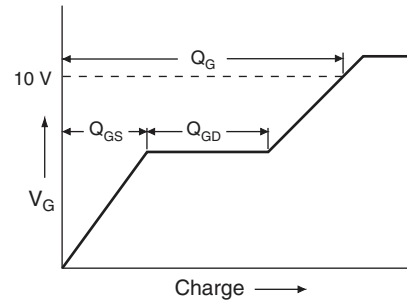


Fig. 16 - Basic Gate Charge Waveform

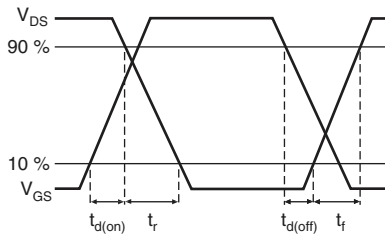


Fig. 13 - Switching Time Waveforms

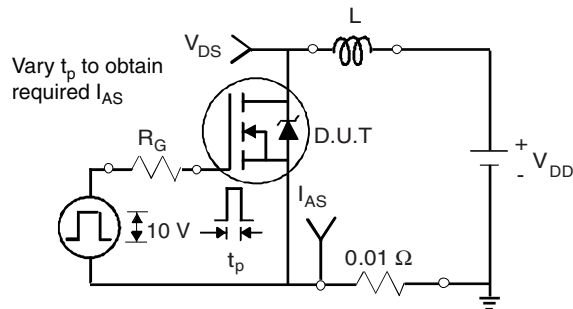


Fig. 14 - Unclamped Inductive Test Circuit

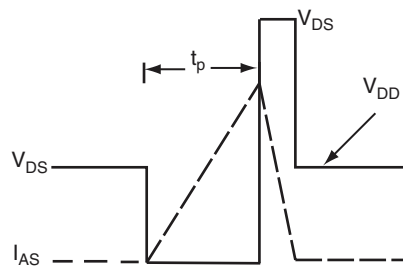


Fig. 15 - Unclamped Inductive Waveforms

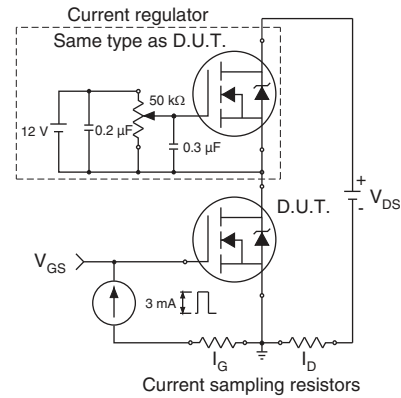


Fig. 17 - Gate Charge Test Circuit



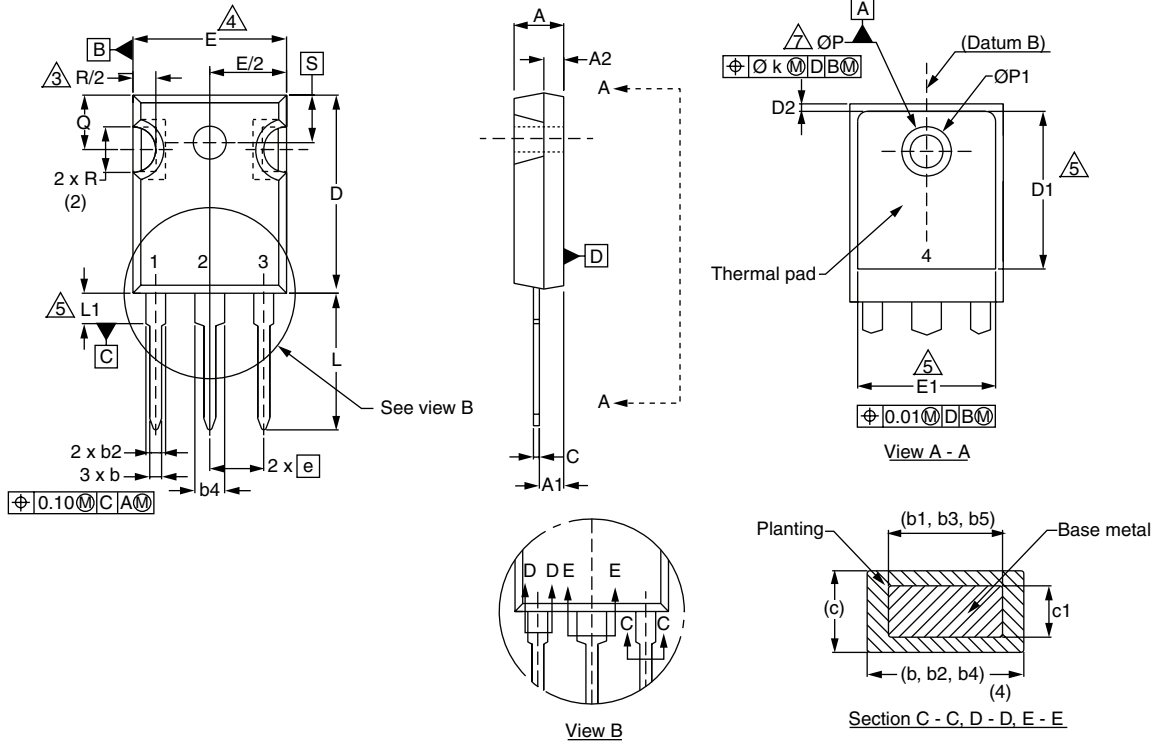
**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

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### TO-247AC (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.65	5.31	0.183	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.65	2.39	0.065	0.094
b3	1.65	2.37	0.065	0.093
b4	2.59	3.43	0.102	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.70	0.776	0.815
D1	13.08	-	0.515	-

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
$\phi k$	0.254		0.010	
L	14.20	16.10	0.559	0.634
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
$\phi P$	3.56	3.66	0.140	0.144
$\phi P1$	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

ECN: S-81920-Rev. A, 15-Sep-08  
DWG: 5971

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6.  $\phi P$  to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.



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- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
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- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
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